

EE330 HW3 Solutions

Problem 1

1) b) $Y = \overline{(AB + C)} \cdot D$

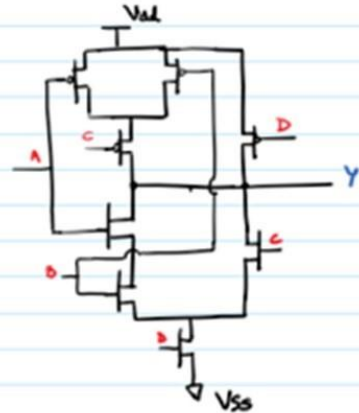
Compound gate approach

Pull Down n/w

$$\bar{Y} = (A \cdot B + C) \cdot D$$

Pull up n/w

$$\begin{aligned} \bar{\bar{Y}} &= \overline{(A \cdot B + C) \cdot D} \\ &= \overline{(A \cdot B) \cdot C} + \bar{D} \\ &= ((\bar{A} \cdot \bar{B}) \cdot \bar{C}) + \bar{D} \\ &= ((\bar{A} + \bar{B}) \cdot \bar{C}) + \bar{D} \end{aligned}$$

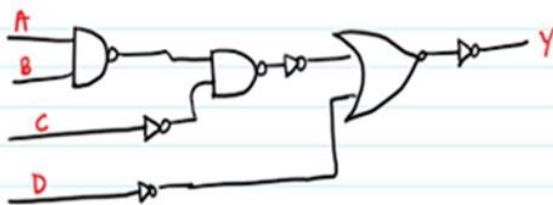


Total no of transistors = 8

Number of logic gates = 1 level of logic

Static CMOS Gate

$$\begin{aligned} Y &= \overline{(AB + C)} \cdot D = \overline{(AB + C)} + \bar{D} \\ &= (\bar{A} \cdot \bar{B} \cdot \bar{C}) + \bar{D} \end{aligned}$$

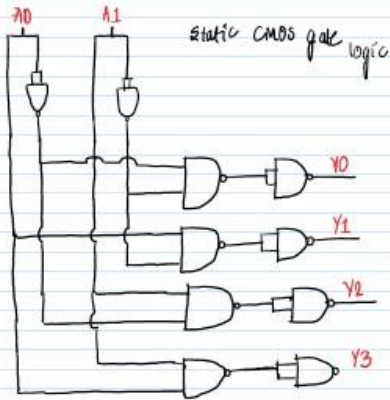
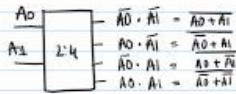


Total no of transistors = 20

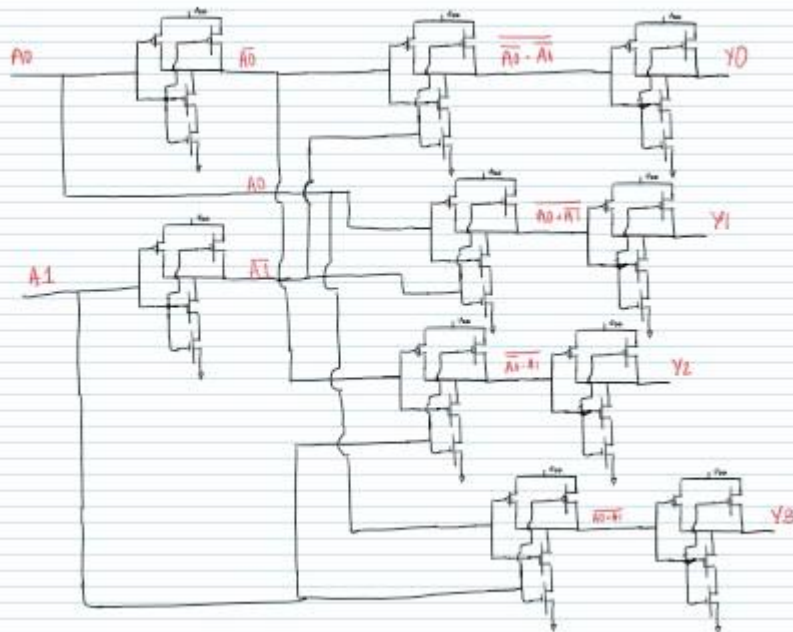
Number of logic gates = 5 level of logic

Problem 2

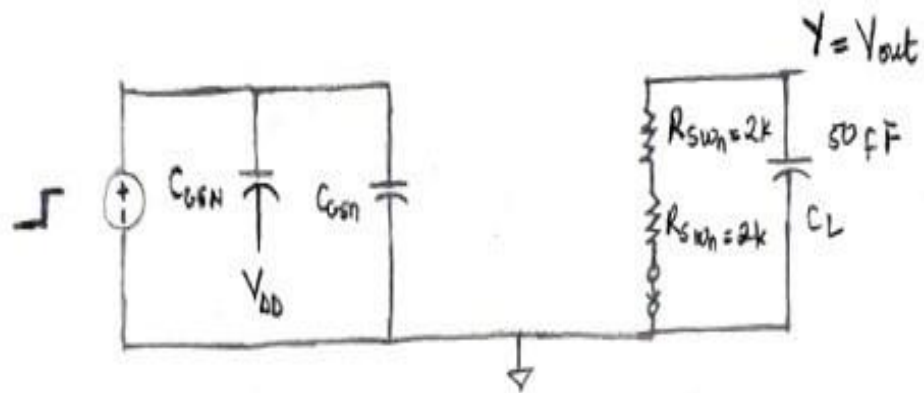
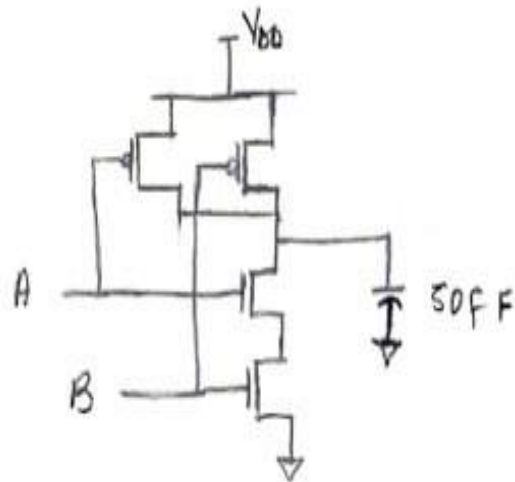
2)



transistor level logic.

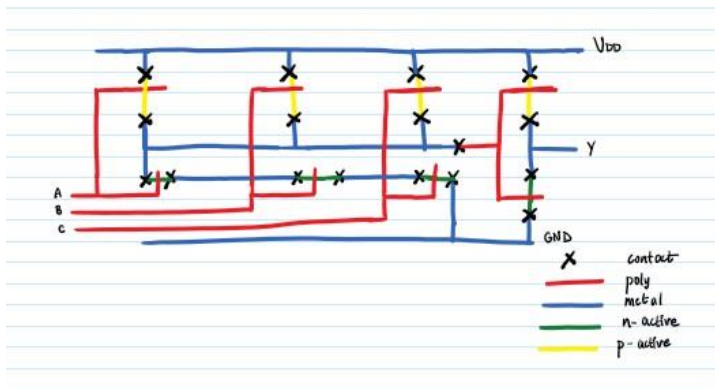
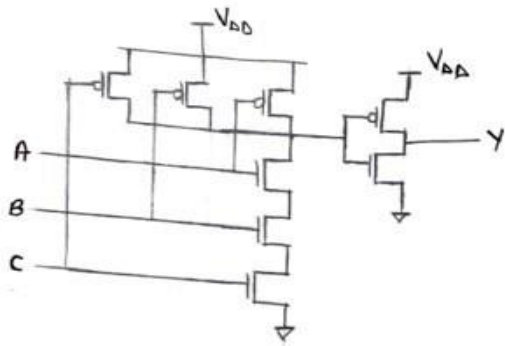


Problem 3

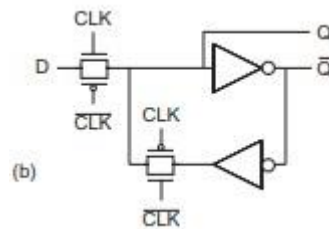
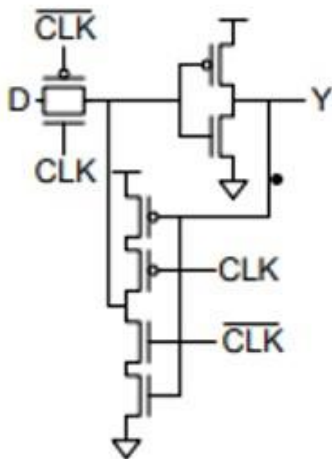


$$\Rightarrow t_{HL} = R_{sw} C_L = (2k + 2k) 50 \times 10^{-15} = \underline{\underline{2 \times 10^{-10} \text{ seconds}}}$$

Problem 4



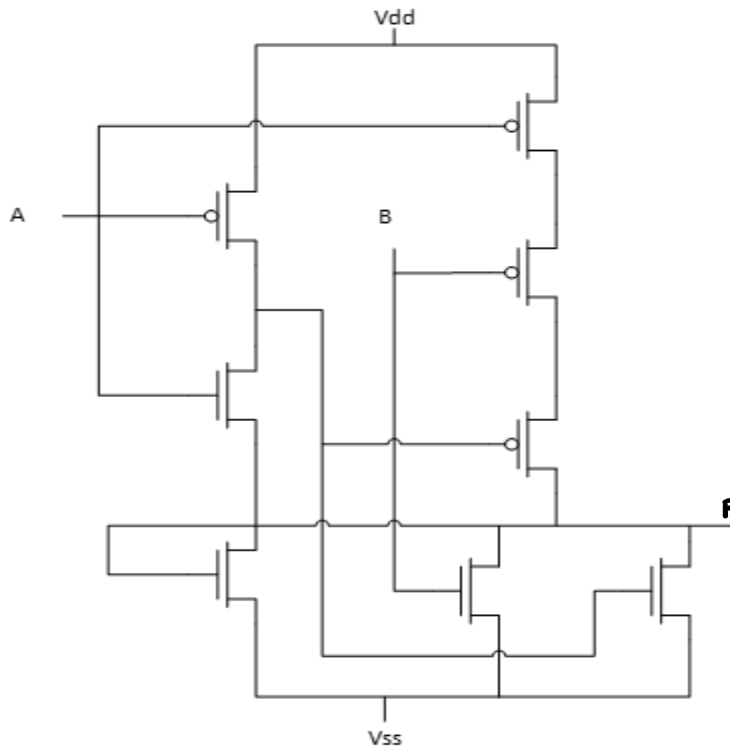
Problem 5



We can see that the figure of 1.31b)

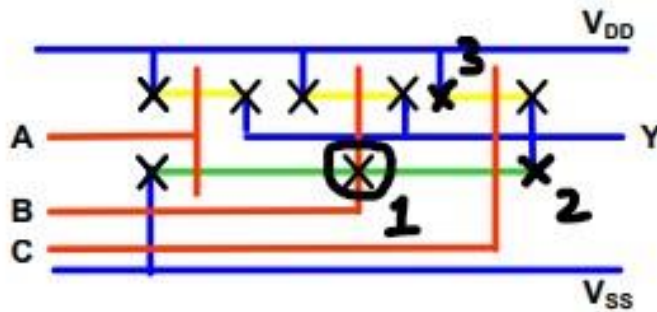
has 2 not gates and 2 T-gates.

Problem 6



Problem 7

For this stick diagram there are 3 errors:



1. No need of contact poly to n-active.
2. Contact needed for Metal 1 to n-active.
3. Contact needed for Metal 1 to p-active.

Problem 8

Assuming ON 0.5 μ m process, $C_{IN} = 1.5fF$, $R_{SWP} = 6k\Omega$, and $R_{SWN} = 2k\Omega$

Total C_{IN} of 6 driven inverters = $C_{IN} * 6$ inverters * 2 transistors/inverter = 18fF = C_L

If input steps from 5V to 0V, transition at output will be from 0V to 5V, so we will be calculating t_{LH}

From lecture, $t_{LH} = C_L * R_{SWP} = 18fF * 6k\Omega = 108$ picoseconds

Problem 9

For this problem, there are three concepts to keep in mind

- Any interconnect will act as a resistor
- Conductivity is the inverse of resistivity
- Interconnect area = $5\mu m * 0.2\mu m = 1\mu m^2$

a) Resistivity of aluminum = $\frac{1 \text{ ohm}}{38 \mu m}$

$$\text{Resistance} = \frac{\rho L}{A}$$

$$\text{Resistance of first segment} = \frac{\left(\frac{1}{38}\right)(180+40)}{1} = \frac{220}{38} = 5.7895 \text{ ohms}$$

$$\text{Resistance of second segment} = \frac{\left(\frac{1}{38}\right)(80)}{1} = \frac{80}{38} = 2.1053 \text{ ohms}$$

$$\text{Voltage across resistor} = 5V * \frac{50 \text{ ohms}}{(50+5.7895+2.1053)\text{ohms}} = 4.3182V$$

b) Resistivity of copper = $\frac{1 \text{ ohm}}{58 \mu m}$

$$\text{Resistance of first segment} = \frac{\left(\frac{1}{58}\right)(180+40)}{1} = \frac{220}{58} = 3.7931 \text{ ohms}$$

$$\text{Resistance of second segment} = \frac{\left(\frac{1}{58}\right)(80)}{1} = \frac{80}{58} = 1.3793 \text{ ohms}$$

$$\text{Voltage across resistor} = 5V * \frac{50 \text{ ohms}}{(50+3.7931+1.3793)\text{ohms}} = 4.5313V$$

Problem 10

```
/*structural implementation of  $f=(!a*b*c)+(a*b!*c)$ 
```

```
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```

```
`timescale 1ns/1ps //set timescale to something nice for simulation
module hw3q10(A, B, C, F); //define module and IO
    input A, B, C; //define A, B, and C as inputs
    output F; //define F as an output
    wire and1, and2; //define intermediary wires to be used
    and(and1, ~A, B, C); //and1 =  $A!B*C$ 
    and(and2, A, B, ~C); //and2 =  $A*B!*C$ 
    or(F, and1, and2); //F = and1 + and2 =  $(A!B*C) + (A+B!*C)$ 
endmodule //end the module
```

```
/*behavioral implementation of  $f=(!a*b*c)+(a*b!*c)$ 
```

```
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```

```
`timescale 1ns/1ps //set timescale to something nice for simulation
module hw3q10(A, B, C, f); //define module and IO

    input A, B, C; //define A, B, and C as inputs
    output F; //define F as an output
    reg out; //define an output register for used
    assign F = out; //assign output register to given output
    always @ (A or B or C) begin //when inputs change, execute the following
        out = (~A&B&C) + (A&B&~C); //f =  $(!A*B*C)+(A*B!*C)$ 
    end //end of preceding always block
endmodule //end the module
```

```
/*standard 3-input logic testbench
```

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EE330 - Integrated Electronics
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Nickolas Moser
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February 2, 2022*/
```

```
`timescale 1ns/1ps //set timescale to something nice to simulate
```

```
module standard_tb(); //instantiate testbench module
```

```

reg a_in, b_in, c_in; //define input registers

wire out; //define output wire

hw3q10 DUT(.A(a_in), .B(b_in), .C(c_in), .F(out)); //instantiate Device Under Test

initial a_in = 0; //set initial input values
initial b_in = 0; initial c_in = 0;

always #1 a_in = ~a_in; //for input n, toggle every 2^n time units
always #2 b_in = ~b_in;
always #4 c_in = ~c_in;

endmodule //end testbench module

```

